Please add the following new claims.

28. The method of claim 16 wherein the photoresist coating layer is exposed with radiation having a wavelength of 300 nm or less.

29. The method of claim 16 wherein the photoresist coating layer is exposed with radiation of a wavelength of 248 nm or less.

30. The method of claim 16 wherein the substrate is a microelectronic wafer substrate.

B3

31. The method of claim 16 wherein the polymer has a weight average molecular weight of at least about 7,000.

32. The method of claim 16 wherein the polymer has a weight average molecular weight of at least about 8,000.

33. The method of claim 16 wherein the polymer is an anthracene acrylic copolymer.

34. The method of claim 16 wherein the photoactive component is a photoacid generator compound.

35. The method of claim 16 wherein the photoactive compound is an onium salt, a nitrobenzyl ether, an s-triazine compound, or a halogenated non-ionic photoacid generating compound.

36. The method of claim 16 wherein the photoresist is a chemically-amplified postive-acting resist.

37. The method of claim 16 wherein the photoresist is a negative-acting resist.

38. The method of claim 17 wherein the photoresist coating layer is exposed with radiation having a wavelength of 300 nm or less.

39. The method of claim 17 wherein the photoresist coating layer is exposed with radiation of a wavelength of 248 nm or less.

B3 contd

40. The method of claim 17 wherein the substrate is a microelectronic wafer substrate.

41. The method of claim 17 wherein the polymer has a weight average molecular weight of at least about 7,000.

42. The method of claim 17 wherein the polymer has a weight average molecular weight of at least about 8,000.

43. The method of claim 17 wherein the photoactive component is a photoacid generator compound.

44. The method of claim 17 wherein the photoactive compound is an onium salt, a nitrobenzyl ether, an s-triazine compound, or a halogenated non-ionic photoacid generating compound.

45. The method of claim 17 wherein the photoresist is a chemically-amplified postive-acting resist.

46. The method of claim 17 wherein the photoresist is a negative-acting resist.

47. The article of claim 20 wherein the photoactive component is a photoacid generator compound.

48. The article of claim 20 wherein the photoactive compound is an onium salt, a nitrobenzyl ether, an s-triazine compound, or a halogenated non-ionic photoacid generating compound.

49. The photoresist composition of claim 22 wherein the photoactive compound is an onium salt, a nitrobenzyl ether, an s-triazine compound, or a halogenated non-ionic photoacid generating compound.

50. A method for forming a photoresist relief image comprising:

applying a coating layer of a photoresist composition on an integrated circuit subtrate or a liquid crystal display substrate, the photoresist composition comprising a resin binder, a photoactive component and a polymeric dye that contains one or more polycyclic chromophores, said dye compound being a polymer wherein the polymer has a weight average molecular weight of at least about 5,000.

51. The method of claim 50 wherein the photoresist coating layer is exposed with radiation having a wavelength of 300 nm or less.

52. The method of claim 50 wherein the photoresist coating layer is exposed with radiation of a wavelength of 248 nm or less.

53. The method of claim 50 wherein the substrate is a microelectronic wafer substrate.

54. The method of claim 50 wherein the polymer has a weight average molecular weight of at least about 7,000.

B3 cont'd

55. The method of claim 50 wherein the polymer has a weight average molecular weight of at least about 8,000.

56. The method of claim 50 wherein the photoactive component is a photoacid generator compound.

57. The method of claim 50 wherein the photoactive compound is an onium salt, a nitrobenzyl ether, an s-triazine compound, or a halogenated non-ionic photoacid generating compound.

58. The method of claim 50 wherein the photoresist is a chemically-amplified postive-acting resist.

59. The method of claim 50 wherein the photoresist is a negative-acting resist.

REMARKS

Applicants appreciate the further indication of allowable subject matter, i.e. that 1, 4-15, 18 and 19 remain allowable, and that claims 24 and 27 would be allowable if rewritten in independent form.

Applicants also submit herewith a Supplemental Information Disclosure Statement with the documents cited in the EPO application that claims priority from the present case.